

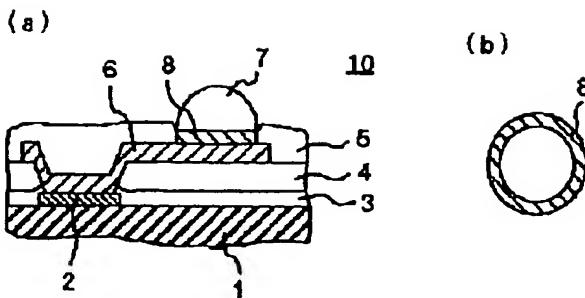
EUROPEAN PATENT OFFICE

Patent Abstracts of Japan

PUBLICATION NUMBER : 2001024021
PUBLICATION DATE : 26-01-01

APPLICATION DATE : 09-07-99
APPLICATION NUMBER : 11195917

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INT.CL. : H01L 21/60 H01L 21/3205
TITLE : SEMICONDUCTOR DEVICE AND
MANUFACTURING METHOD



ABSTRACT : PROBLEM TO BE SOLVED: To provide a semiconductor device at a low cost and its manufacturing method for reducing stress caused by the difference in coefficient of thermal expansion with a mounting substrate surely.

SOLUTION: A semiconductor device includes an electrode part 2 on a semiconductor element 1, a wiring layer 6 connected to the electrode part 2 via an insulating layer 4, and a package electrode 7 formed on the wiring layer 6. A conductive member 8 made of alloy with martensitic transformation is placed partly in a conductive path from the wiring layer 6 to the package electrode 7 to absorb stress caused in the conductive path. In this way, a semiconductor device with reliability in connection, superior electrical characteristics and suitability in high-density mounting can be obtained at a low cost. As a result, the semiconductor device can be connected with a wiring board, using solder to complete high-performance electronic apparatus.

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